



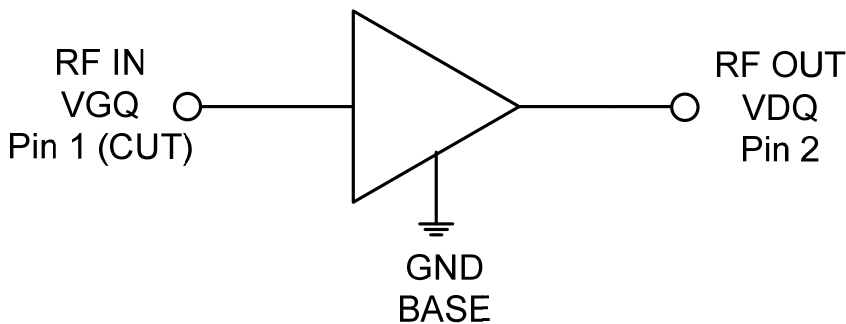
Package: Flanged Ceramic, 2-pin, RF360-2

**Features**

- Broadband Operation
  - Tunable from DC to 4GHz
  - Instantaneous: 800MHz to 2500MHz
- Advanced GaN HEMT Technology
- Peak Modulated Power >30W
- Advanced Heat-Sink Technology
- 48V Typical Modulated Performance
  - P<sub>OUT</sub> 39.5dBm
  - Gain 14.5dB
  - Drain Efficiency 35%
  - ACP -40dBc
- 48V Typical CW Performance
  - P<sub>OUT</sub> 45.5dBm
  - Gain 15dB
  - Drain Efficiency 56%
- -40 °C to 85 °C Operating Temperature

**Applications**

- Civilian and Military Radar
- Military Communications
- General Purpose Broadband Amplifiers
- Electronic Warfare
- Public Mobile Radios
- Commercial Wireless Infrastructure
- Cellular and WiMAX Infrastructure
- Industrial, Scientific, and Medical



Functional Block Diagram

**Product Description**

The RFHA3942 is a 48V, 35W high power discrete amplifier designed for military communications, radar, electronic warfare, general purpose broadband amplifier, commercial wireless infrastructure, and industrial/scientific/Medical applications. Using a second generation advanced high power density Gallium Nitride (GaN) semiconductor process with improved linearity, these high-performance amplifiers achieve high efficiency, excellent linearity, and flat gain and power over a broad frequency range in a single amplifier design. The RFHA3942 is an unmatched GaN transistor, packaged in a hermetic flanged ceramic package. This package provides excellent thermal stability through the use of advanced heat sink and power dissipation technologies. Ease of integration is accomplished by incorporating simple, optimized matching networks external to the package that provide wideband gain and power performance in a single amplifier.

**Ordering Information**

RFHA3942	35W GaN Power Amplifier
RFHA3942PCBA-410	Fully Assembled Evaluationat Board Optimized for 2.14GHz; 48V

**Optimum Technology Matching® Applied**

- |                                      |                                      |                                     |  |
|--------------------------------------|--------------------------------------|-------------------------------------|--|
| <input type="checkbox"/> GaAs HBT    | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input checked="" type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS   | <input type="checkbox"/> Si CMOS    | <input type="checkbox"/> BiFET HBT           |
| <input type="checkbox"/> InGaP HBT   | <input type="checkbox"/> SiGe HBT    | <input type="checkbox"/> Si BJT     |  |

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**Please contact  
RFMD Technical Support  
at (336) 678-5570  
for more information.**